

## Dual N-Channel 20 V (D-S) MOSFET

### PRODUCT SUMMARY

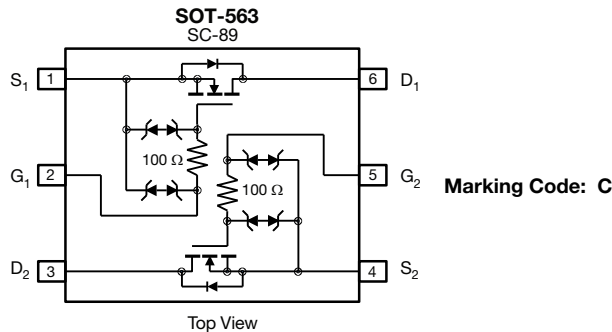
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (mA)
20	0.70 at $V_{GS} = 4.5$ V	600
	0.85 at $V_{GS} = 2.5$ V	500
	1.25 at $V_{GS} = 1.8$ V	350

### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET: 1.8 V Rated
- Very Small Footprint
- High-Side Switching
- Low On-Resistance: 0.7  $\Omega$
- Low Threshold: 0.8 V (typ.)
- Fast Switching Speed: 10 ns
- 1.8 V Operation
- Gate-Source ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**



**Ordering Information:** Si1024X-T1-GE3 (Lead (Pb)-free and Halogen-free)

### BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation

### APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pages

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	20		V	
Gate-Source Voltage	$V_{GS}$	$\pm 6$			
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	515	485	mA
		$T_A = 85$ °C	370	350	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	650			
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	450	380		
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	280	250	mW
		$T_A = 85$ °C	145	130	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C	
Gate-Source ESD Rating (HBM, Method 3015)	ESD	2000		V	

Notes:

- Surface mounted on FR4 board.
- Pulse width limited by maximum junction temperature.

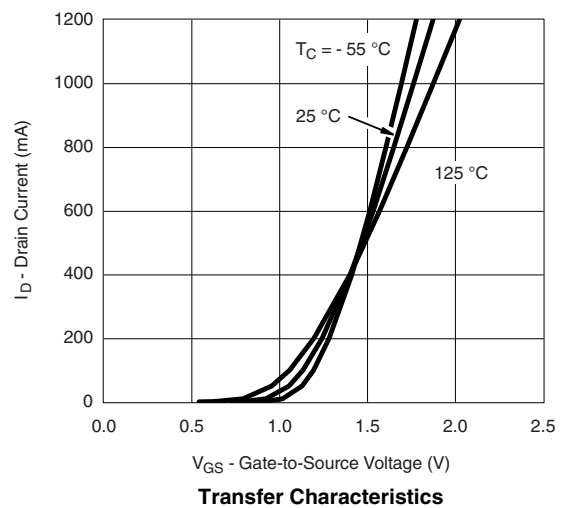
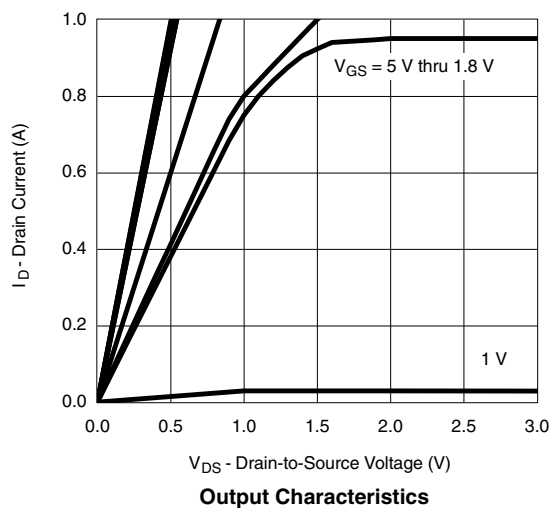
**SPECIFICATIONS** ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	0.45		0.9	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 4.5\text{ V}$		$\pm 0.5$	$\pm 1$	$\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20\text{ V}$ , $V_{GS} = 0\text{ V}$		0.3	100	nA
		$V_{DS} = 20\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 85\text{ }^\circ\text{C}$			5	$\mu\text{A}$
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}$ , $V_{GS} = 4.5\text{ V}$	700			mA
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}$ , $I_D = 600\text{ mA}$		0.41	0.70	$\Omega$
		$V_{GS} = 2.5\text{ V}$ , $I_D = 500\text{ mA}$		0.53	0.85	
		$V_{GS} = 1.8\text{ V}$ , $I_D = 350\text{ mA}$		0.70	1.25	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 10\text{ V}$ , $I_D = 400\text{ mA}$		1		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 150\text{ mA}$ , $V_{GS} = 0\text{ V}$		0.8	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 10\text{ V}$ , $V_{GS} = 4.5\text{ V}$ , $I_D = 250\text{ mA}$		750		pC
Gate-Source Charge	$Q_{gs}$			75		
Gate-Drain Charge	$Q_{gd}$			225		
Turn-On Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}$ , $R_L = 47\text{ }\Omega$ $I_D \approx 200\text{ mA}$ , $V_{GEN} = 4.5\text{ V}$ , $R_g = 10\text{ }\Omega$		10		ns
Turn-Off Time	$t_{d(off)}$			36		

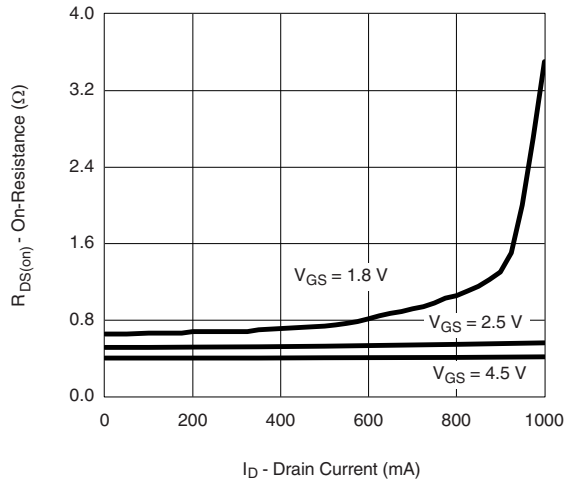
## Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

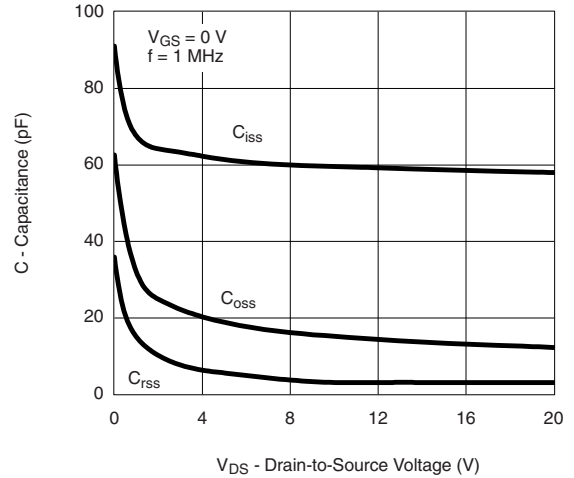
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

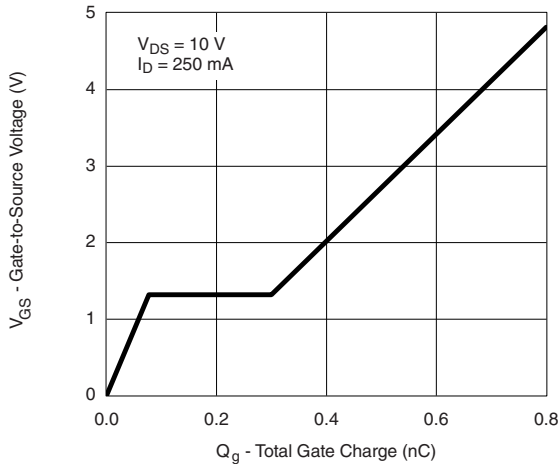
## TYPICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)



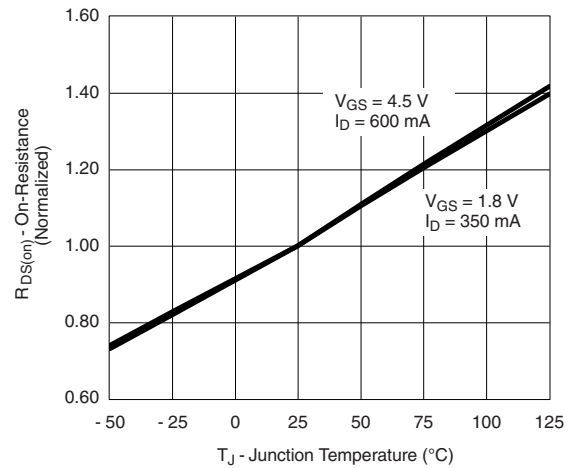
**On-Resistance vs. Drain Current**



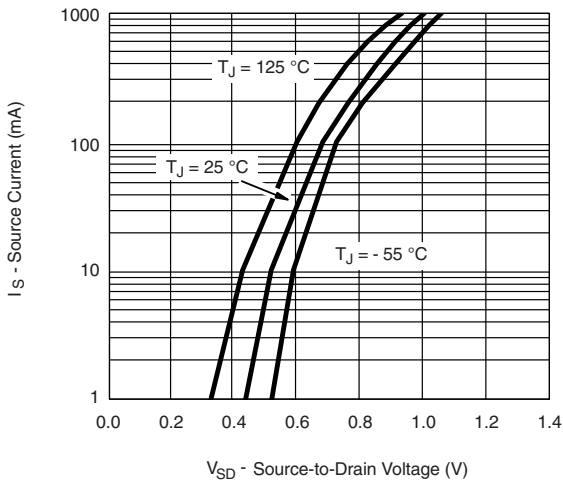
**Capacitance**



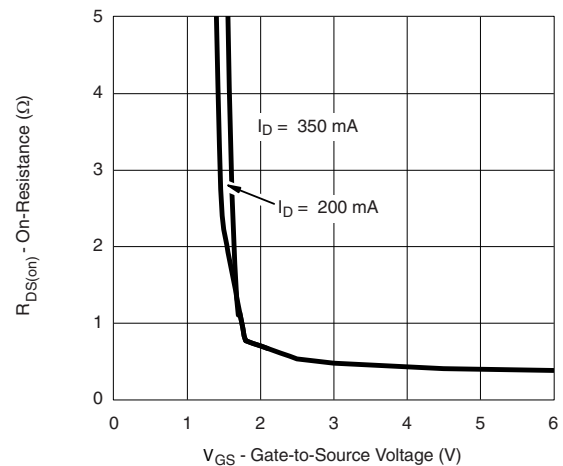
**Gate Charge**



**On-Resistance vs. Junction Temperature**

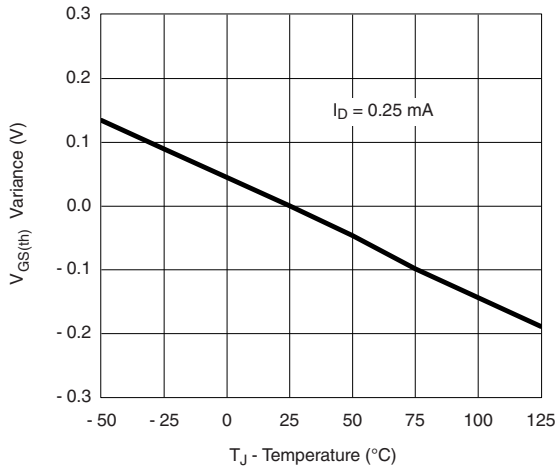


**Source-Drain Diode Forward Voltage**

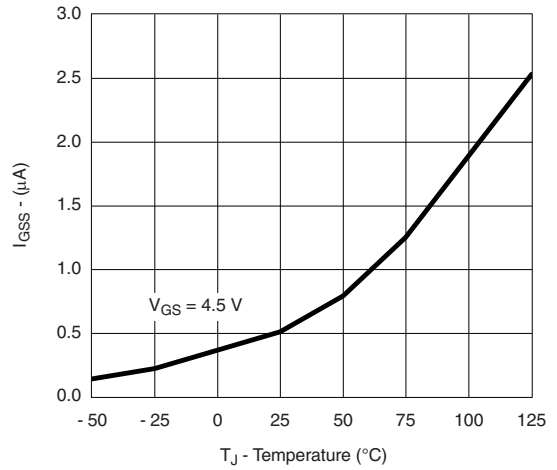


**On-Resistance vs. Gate-to-Source Voltage**

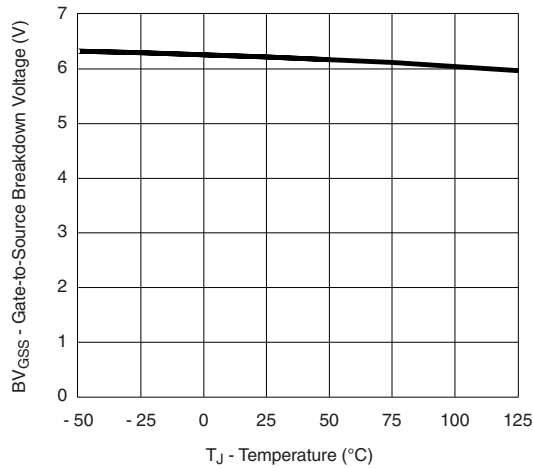
### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



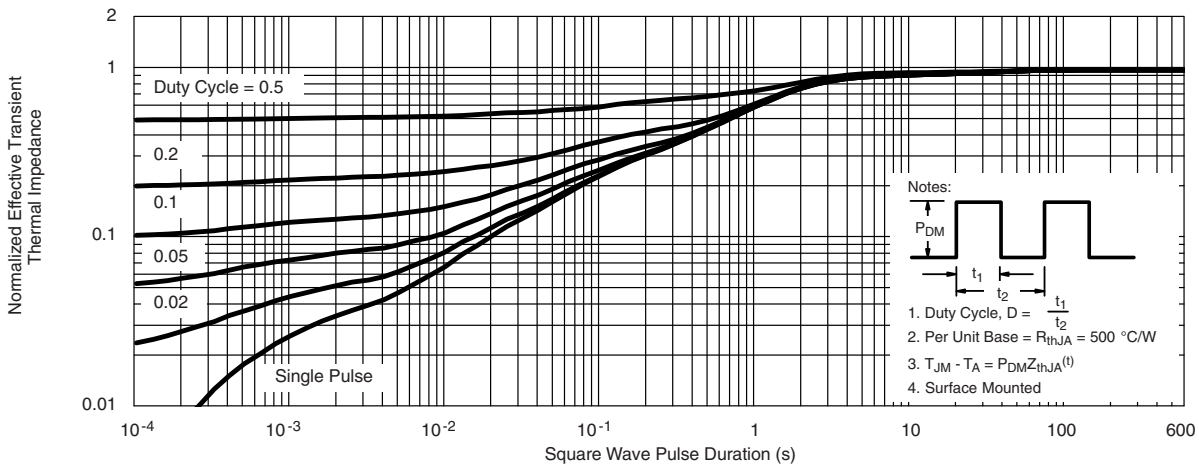
**Threshold Voltage Variance vs. Temperature**



**I<sub>GSS</sub> vs. Temperature**



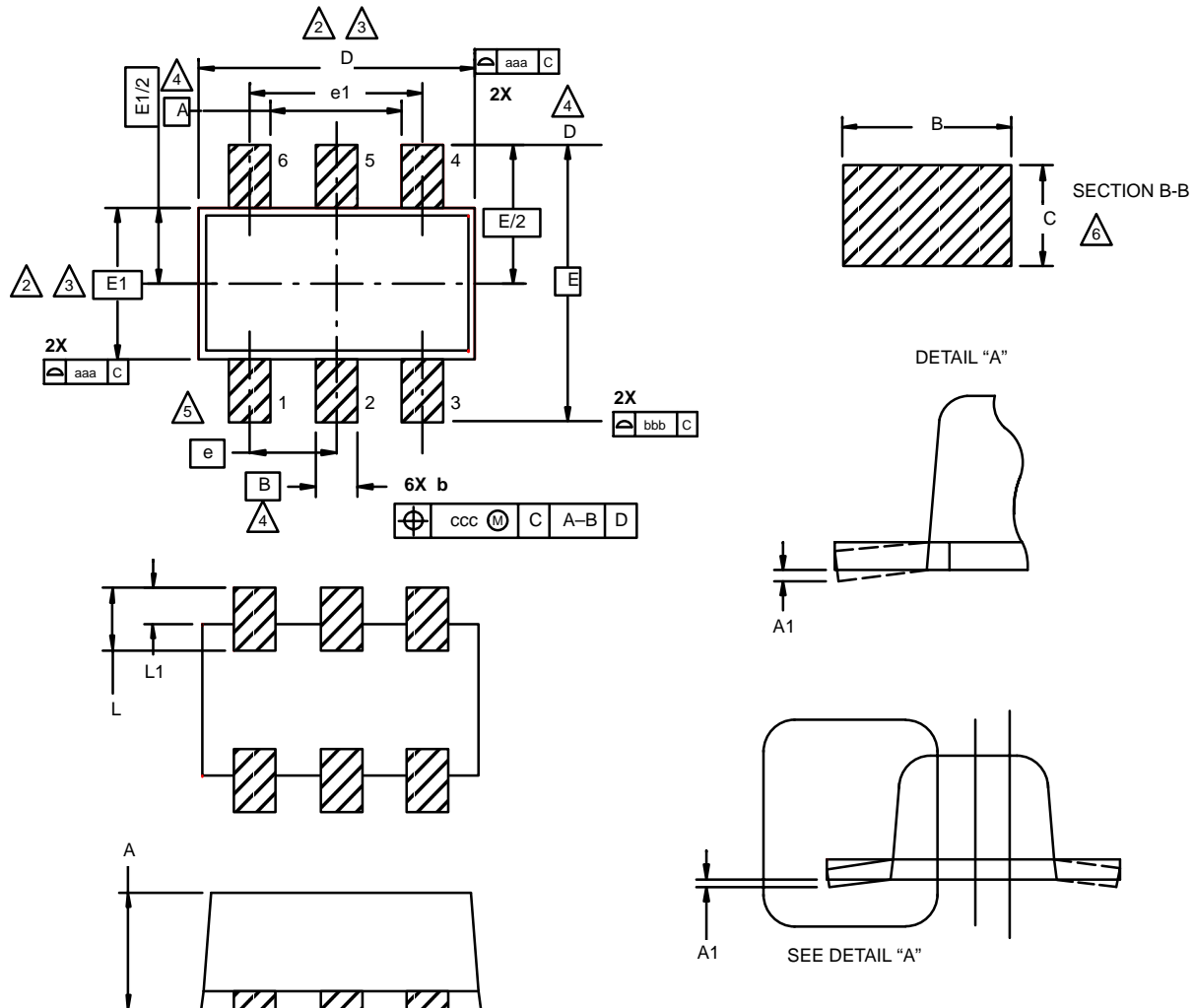
**BV<sub>GSS</sub> vs. Temperature**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

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### SC89: 6- LEADS (SOT-563F)



**NOTES:**

1. Dimensions in millimeters.

**2** Dimension D does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.

**3** Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.

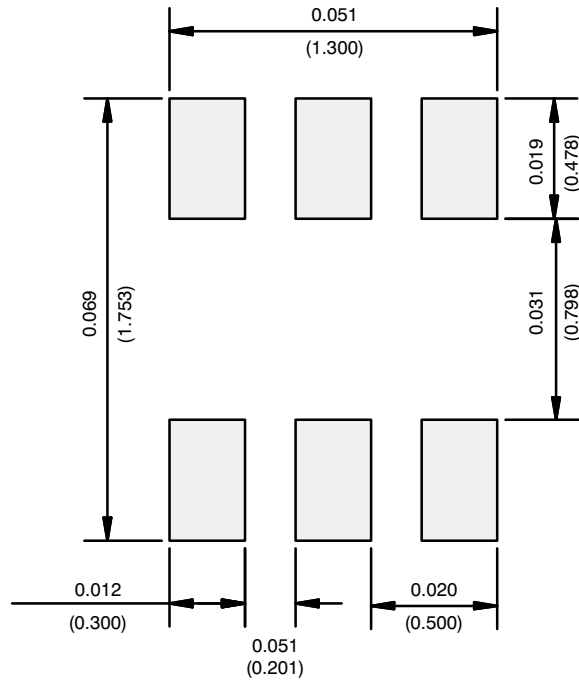
**4** Datums A, B and D to be determined 0.10 mm from the lead tip.

**5** Terminal numbers are shown for reference only.

**6** These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

Dim	MILLIMETERS		Note	Symbol	Tolerances Of Form And Position
	Min	Max			
A	0.56	0.60		aaa	0.10
A1	0.00	0.10		bbb	0.10
b	0.15	0.30		ccc	0.10
c	0.10	0.18			
D	1.50	1.70	2, 3		
E	1.55	1.70			
E1	1.20 BSC		2, 3		
e	0.50 BSC				
e1	1.00 BSC				
L	0.35 BSC				
L1	0.20 BSC				
ECN: E-00499—Rev. B, 02-Jul-01 DWG: 5880					

## RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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